



# FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

## ST 2N3905 / 2N3906

### PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications.

As complementary types the NPN transistors  
2N3903 and 2N3904 are recommended.

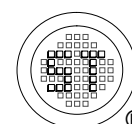
On special request, these transistors can be  
manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	200	mA
Power Dissipation	$P_{tot}$	625	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$





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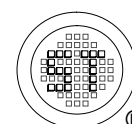
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#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{CE} = 1\text{ V}$ , $-I_C = 0.1\text{ mA}$	2N3905 $h_{FE}$	30	-	-
	2N3906 $h_{FE}$	60	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 1\text{ mA}$	2N3905 $h_{FE}$	40	-	-
	2N3906 $h_{FE}$	80	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 10\text{ mA}$	2N3905 $h_{FE}$	50	150	-
	2N3906 $h_{FE}$	100	300	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 50\text{ mA}$	2N3905 $h_{FE}$	30	-	-
	2N3906 $h_{FE}$	60	-	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$	2N3905 $h_{FE}$	15	-	-
	2N3906 $h_{FE}$	30	-	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$ $-V_{CE(sat)}$	- -	0.25 0.4	V
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$ $-V_{BE(sat)}$	- -	0.85 0.95	V
Gain Bandwidth Product at $-V_{CE} = 20\text{ V}$ , $-I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	2N3905 $f_T$ 2N3906	200 250	- -	MHz
Collector Base Capacitance at $-V_{CB} = 5\text{ V}$ , $f = 100\text{ KHz}$	$C_{ob}$	-	4.5	pF
Delay Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_d$	-	35	ns
Rise Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_r$	-	35	ns
Storage Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_s$	-	225	ns
Fall Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_f$	-	75	ns





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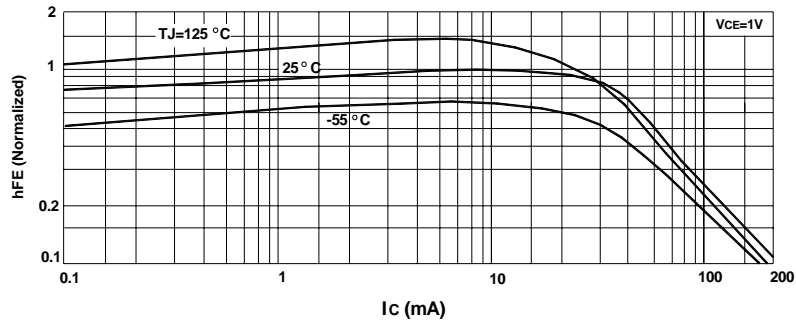
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DC Current Gain



Collector Saturation Region

